

Low voltage fast-switching PNP power transistor

Datasheet - production data

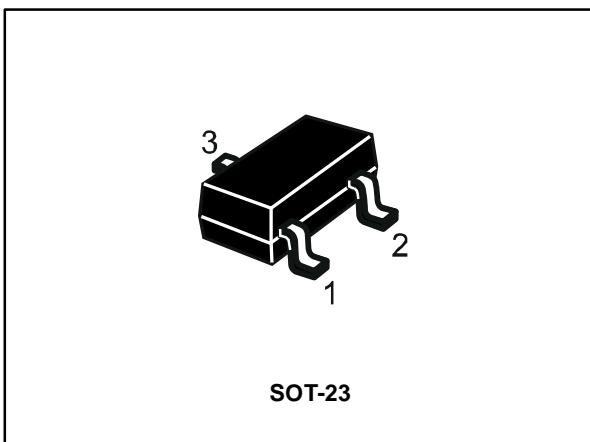
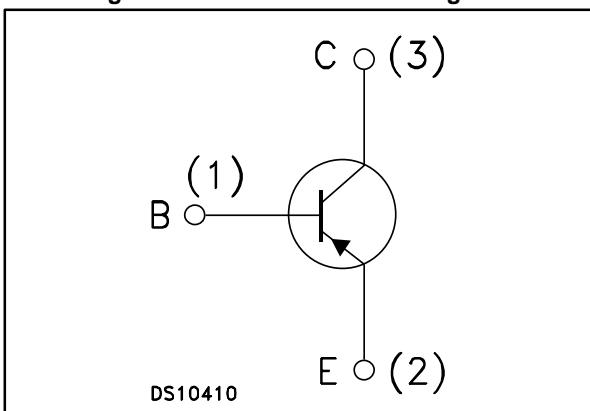


Figure 1: Internal schematic diagram



DS10410

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

Applications

- LED
- Motherboard & hard disk drive
- Mobile equipment
- Battery charger
- Voltage regulation

Description

The device is a PNP transistor manufactured using new “PB-HCD” (power bipolar high current density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

Table 1: Device summary

Order code	Marking	Package	Packing
2STR2230	2230	SOT-23	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{CE} = 0$)	-30	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	-30	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-5	V
I_C	Collector current	-1.5	A
I_{CM}	Collector peak current ($t_P < 5\text{ms}$)	-3	A
P_{tot}	Total dissipation at $T_{amb} = 25^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature range	-65 to 150	$^\circ\text{C}$
T_J	Operating junction temperature range		

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	250	$^\circ\text{C}/\text{W}$

Notes:(1)Device mounted on PCB area of 1 cm^2

2 Electrical characteristics

($T_{case} = 25^\circ C$ unless otherwise specified)

Table 4: Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{CB} = -30 V$			-0.1	μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = -4 V$			-0.1	μA
$V_{(BR)CBO}$	Collector-base breakdown voltage ($I_E = 0$)	$I_C = -100 \mu A$	-30			V
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = -10 mA$	-30			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage ($I_C = 0$)	$I_E = -100 \mu A$	-5			V
$V^{(1)}$	Collector-emitter saturation voltage	$I_C = -0.1 A, I_B = -1mA$			-0.17	mV
		$I_C = -1 A, I_B = -100mA$		-0.25	-0.45	
		$I_C = -2 A, I_B = -200mA$		-0.42	-0.8	
$V_{BE(sat)}^{(1)}$	Base-emitter saturation voltage	$I_C = -1 A, I_B = -100 mA$		-0.9	-1.25	V
$h_{FE}^{(1)}$	DC current gain	$I_C = -50 mA, V_{CE} = -2V$	210			
		$I_C = -0.5 A, V_{CE} = -2V$	170	280	560	
		$I_C = -1 A, V_{CE} = -2V$	100			
		$I_C = -1.5 A, V_{CE} = -2V$	70			
f_t	Transition frequency	$I_C = -0.1 A, V_{CE} = -5 V$ $f = 100 MHz$	100			MHz
C_{CBO}	Collector-base capacitance	$I_E = 0, V_{CB} = -10 V$ $f = 1 MHz$		10		pF
t_{on}	Turn-on time	Resistive load $I_C = -1.5 A, V_{CC} = -10 V$ $I_{B1} = -I_{B2} = -150 mA$		74		ns
t_{off}	Turn-off time			200		ns

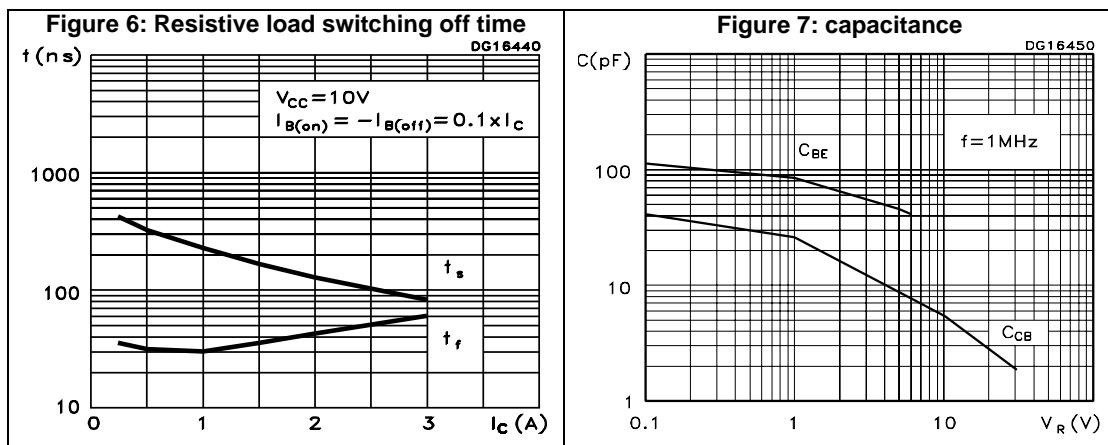
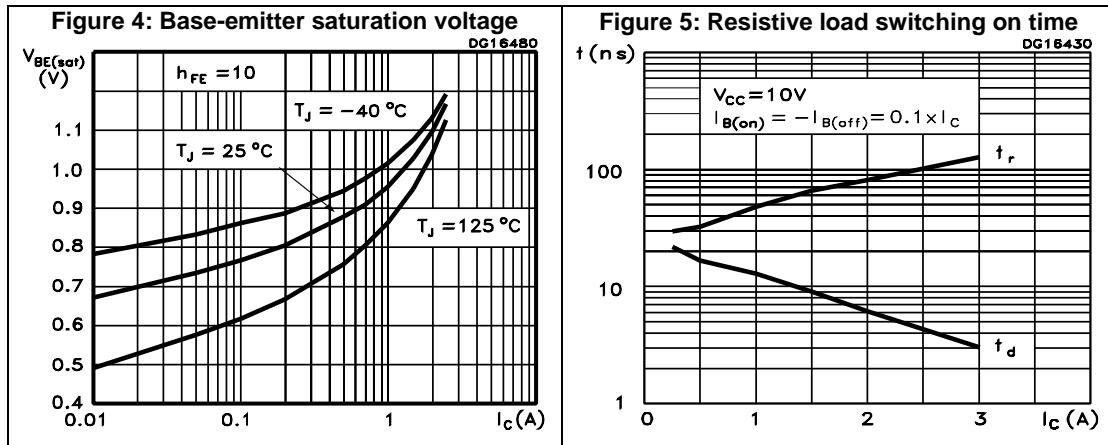
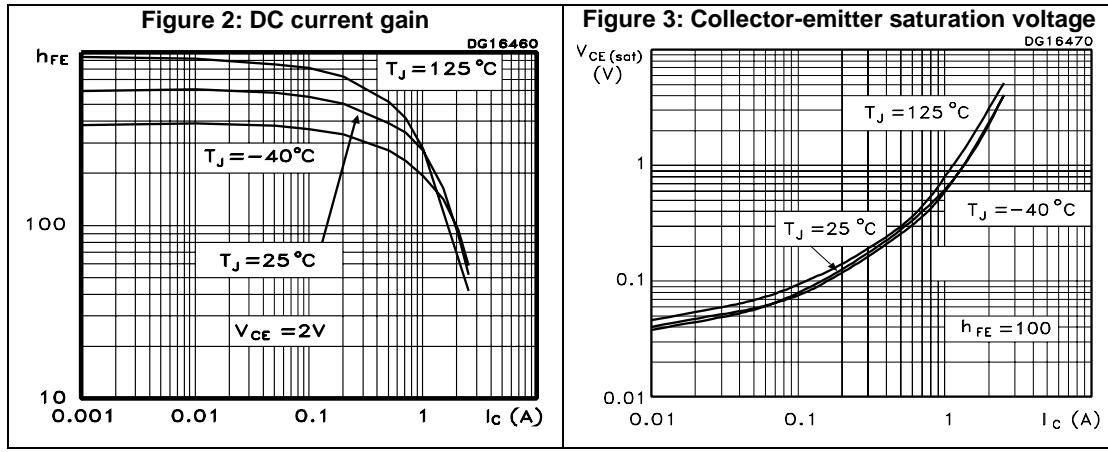
Notes:

(¹)Pulse test: pulse duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)



For the PNP transistors, current and voltage polarities are reversed.



3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
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3.1 SOT-23 package information

Figure 8: SOT-23 package outline

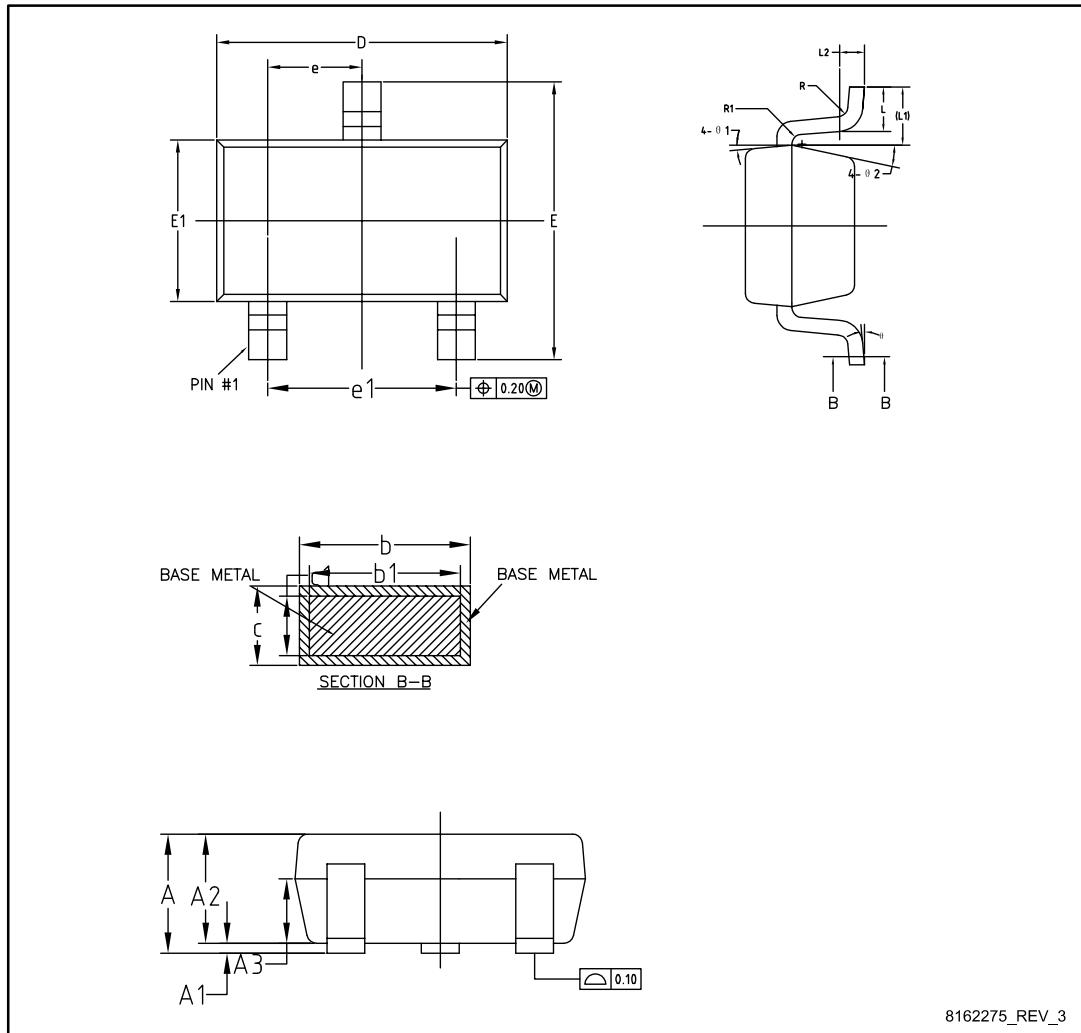
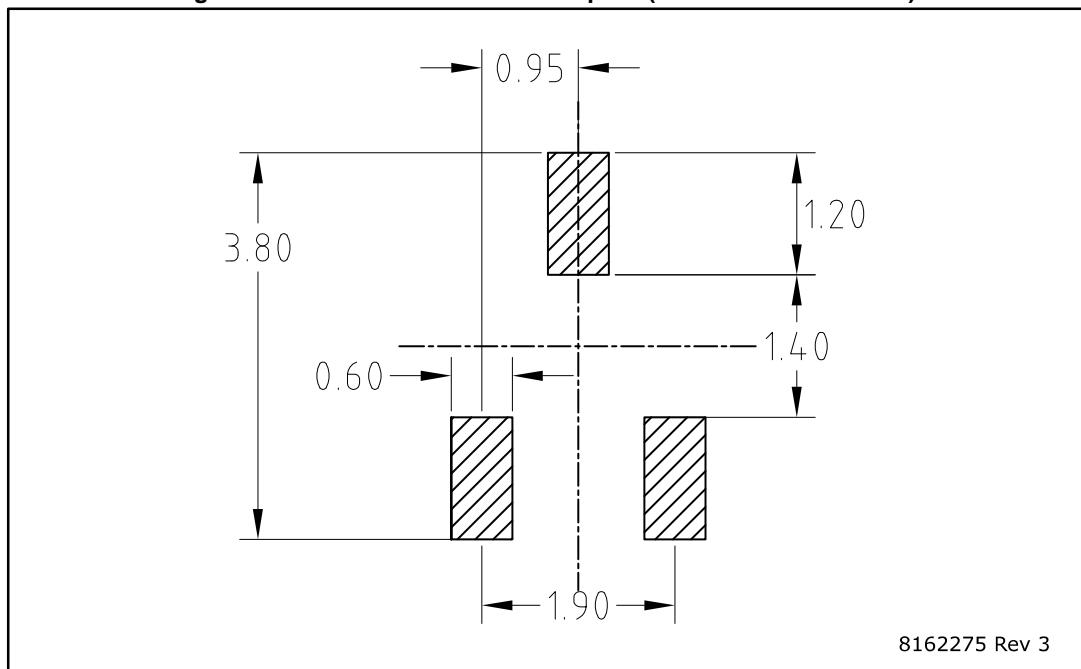


Table 5: SOT-23 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A			1.25
A1	0		0.15
A2	1	1.10	1.20
A3	0.60	0.65	0.70
b	0.36		0.50
b1	0.36	0.38	0.45
c	0.14		0.20
c1	0.14	0.15	0.16
D	2.826	2.926	3.026
E	2.60	2.80	3.00
E1	1.526	1.626	1.726
e	0.90	0.95	1.00
e1	1.80	1.90	2.00
L	0.35	0.45	0.60
L1		0.59 REF	
L2		0.25 BSC	
R	0.05		
R1	0.05		
θ	0°		8°
θ_1	3°	5°	7°
θ_2	6°		5°

Figure 9: SOT-23 recommended footprint (dimensions are in mm)



4 Revision history

Table 6: Document revision history

Date	Revision	Changes
18-Jul-2006	1	Initial release
31-Oct-2006	2	New graphics
07-Nov-2006	3	Maturity changed from preliminary to full.
09-Jun-2016	4	Updated features and description in cover page. Updated Table 1: "Device summary" . Updated Section 3.1: "SOT-23 package information" . Minor text changes.

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